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 $^{53}\mathrm{S.}$  L. Norman and D. H. Douglass, Jr., Phys. Rev. Letters 18, 339 (1966).

<sup>54</sup>See, for example, Ref. 15 comments to this effect.  ${}^{55}$ E. Abrahams and T. Tsuneto, Phys. Rev. <u>152</u>, 416 (1966).

<sup>56</sup>P. C. Hohenberg, Phys. Rev. 158, 383 (1967).

<sup>57</sup>H. J. Mikeska and H. Schmidt (private communica-

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## Thermodynamics of Pressure Effects in V<sub>3</sub>Si and V<sub>3</sub>Ge

L. J. Sham<sup>\*</sup> and T. F. Smith<sup> $\dagger$ </sup>

Department of Physics and Institute for Pure and Applied Physical Sciences, University of California, San Diego, La Jolla, California 92037 (Received 3 June 1971)

The thermodynamic relationships relating the pressure dependence of the superconducting transition temperature to the changes in the elastic constants at the transition are presented and their application to the compounds  $V_3$ Si and  $V_3$ Ge is discussed.

In a series of recent  $articles^{1-3}$  Testardi and coworkers have made predictions of an unusually large quadratic strain dependence of the superconducting transition temperature for the A15 superconductors  $V_3$  Si and  $V_3$  Ge.<sup>4</sup> Measurements<sup>5, 6</sup> of  $T_c$  as a function of pressure for these compounds fail to reveal any evidence of the quadratic dependence, with  $T_c$ increasing linearly with pressure for both compounds. Since the predicted behavior follows directly from a purely thermodynamic treatment of the elastic properties, as determined from sound velocity measurements close to  $T_c$ , and is, therefore, completely model independent, the conflict is of the most fundamental nature. It is the purpose of this paper to make a critical evaluation of the circumstances surrounding the discrepancy in an attempt to isolate its origin.

We shall begin by considering the appropriate thermodynamic relationships linking the discontinuities in the compressibility and its temperature derivative at the superconducting transition with the pressure derivatives of  $T_c$ . Starting with the difference in the Gibb's energy between the normal (n) and superconducting states (s),<sup>7</sup>

$$G_n(T) - G_s(T) = \frac{V}{8\pi} H_c(T)^2$$
,

and successively differentiating with respect to T and P we obtain expressions for the change in specific heat C, compressibility  $\kappa$ , thermal expansion  $\alpha$ , and their various derivatives, in going from the superconducting to the normal state.

We have taken the temperature dependence of  $H_c$  to be of the general form

$$H_c(T) = B_1(T_c - T)/T_c + \frac{1}{2}B_2(T_c - T)^2/T_c^2 + \cdots,$$

where the coefficients  $B_n$  are temperature independent. Although this expansion may be related to the more usual quadratic form

<sup>58</sup>W. E. Masker, S. Marĉelja, and R. D. Parks, Phys.

<sup>59</sup>P. Fulde and K. Maki, Physik Kondensierten Materie

<sup>60</sup>P. G. de Gennes and S. Mauro, Solid State Commun.

$$H_c(T) = H_0(1 - T^2/T_c^2)$$

by putting  $B_1 = 2H_0$  and  $B_2 = -2H_0$  we prefer to avoid this more restricted expression and obtain values for  $B_1$  and  $B_2$  from the heat-capacity data available using (1) and (2) given below. In actual practice we find that the values we obtain for  $B_1$  and  $B_2$  lead to a temperature dependence of  $H_c$  which is not very different from the quadratic form. It may be readily determined that at  $T = T_c$ 

$$C_n - C_s = -\frac{V}{4\pi} \left(\frac{B_1}{T_c}\right)^2,\tag{1}$$

$$\frac{\partial}{\partial T} (C_n - C_s) = -\frac{V}{4\pi} (1 + 3\alpha T_c) \left(\frac{B_1}{T_c}\right)^2 + \frac{3}{4\pi} \frac{B_1 B_2}{T_c^2} , \qquad (2)$$

$$\kappa_n - \kappa_s = -\frac{1}{4\pi} \left(\frac{B_1}{T_c}\right)^2 \left(\frac{\partial T_c}{\partial P}\right)^2, \qquad (3)$$

$$\frac{\partial}{\partial T} (\kappa_n - \kappa_s) = \frac{1}{4\pi} \left( \frac{B_1}{T_c} \right)^2 \frac{\partial^2 T_c}{\partial P^2} + \frac{3}{4\pi} \frac{B_1 B_2}{T_c^3} \left( \frac{\partial T_c}{\partial P} \right)^2 \\ + \left[ \frac{B_1}{\pi T_c} \frac{\partial}{\partial P} \left( \frac{B_1}{T_c} \right) - \frac{\kappa_s}{2\pi} \left( \frac{B_1}{T_c} \right)^2 \right] \left( \frac{\partial T_c}{\partial P} \right).$$
(4)

On comparing (4) with the equivalent relationship derived by Testardi<sup>2</sup> we find only the first term on the right-hand side.<sup>7</sup> The loss of the term in  $(\partial T_c/\partial P)^2$  may be traced to his approximation that  $H_c(T) = 2H_0(1 - T/T_c)$ , which is equivalent to taking  $B_2=0$ . Since we find that  $B_2 \simeq -B_1$  for both com-

	V <sub>3</sub> Ge	V <sub>3</sub> Si
<i>T<sub>c</sub></i> (°K)	6.1	16.9
$\beta (10^{12} \text{ dyn cm}^{-2})$	1.73	1.71
$C_s - C_n (10^4 \text{ dyn cm}^{-2} \text{deg}^{-1})$	9.25	76.6
$\frac{\partial}{\partial T} (C_s - C_n) (10^4 \mathrm{dyn}\mathrm{cm}^{-2}\mathrm{deg}^{-2})$	5.71	16.0
$\frac{1}{4\pi} \left(\frac{B_1}{T_c}\right)^2 (10^4 \text{ dyn cm}^{-2} \text{ deg}^{-2})$	1.52	4.56
$B_1/B_2$	-0.92	-0.85

TABLE I. Quantities used in the relationships (3) and (4).

pounds under consideration, such an approximation is not valid. The third term does appear in his derivation, but it was argued that it was small enough to be neglected. Taking  $B_1 \simeq 2H_0$  and using the relationship  $H_0/T_c \propto \gamma^{1/2}$  (where  $\gamma$  is the coefficient of the linear term in the low-temperature heat capacity) the coefficient of this term may be rewritten as

$$\frac{\kappa_s}{2\pi} \left(\frac{B_1}{T_c}\right)^2 \left(\gamma_e - 1\right) ,$$

where  $\gamma_e = d \ln \gamma/d \ln V$  is the electronic Grüneisen parameter. For any normal value of  $\gamma_e(\sim 1-2)$  the third term will only amount to a few percent of the second term and therefore may be safely neglected, as argued, though somewhat differently, by Testardi.<sup>2</sup> However, in the event that  $\gamma_e$  were anomalously large, say,  $\geq 10$ , then it would be necessary to take this term into consideration.

Using the heat-capacity data of Testardi *et al.*<sup>3</sup> in (1) and (2) we obtain values for  $B_1$  and the ratio  $B_2/B_1$ . Relationships (3) and (4) then enable us to compare the pressure coefficients for  $T_c$  calculated from the elastic data and vice versa. All the relevant quantities used in the calculations are listed in Table I and the results are summarized in Table II. We can only quote upper limits on  $|\partial T_c/\partial P|$  based upon the quoted fractional resolution  $\Delta c/c$  of the elastic measurements, which were  $10^{-5}$  and  $5 \times 10^{-5}$  for V<sub>3</sub>Ge and V<sub>3</sub>Si, respectively, since no discontinuity at  $T_c$  could be detected.<sup>2</sup> The limiting value in the case of V<sub>3</sub>Si is in fairly reasonable agreement with the measured value, but that for  $V_3$  Ge is a factor 3 smaller. In both cases the calculated pressure dependence of  $T_c$  is dominated by a large quadratic term which is positive for  $V_3$  Ge and negative for  $V_3$  Si. The considerable discrepancy between the calculated and observed variation of  $T_c$  with pressure is demonstrated in Fig. 1. The double lines for each calculated dependence reflect the inability to determine the sign of the linear term from (3).

We shall now consider to what extent the latitude in determining the quantities substituted into (3) and (4) can account for the failure to find consistency. Since the discrepancies involved amount to orders of magnitude and the uncertainties in  $B_1$ and  $B_2$  are no more than several percent we will confine our examination to the pressure and elastic data.

In Fig. 1 we show the linear dependences of  $T_c$ upon pressure which were originally reported by one of us.<sup>6</sup> Certainly, in the case of  $V_3$  Ge, there is no evidence to suppose other than a linear variation. However, it must be admitted that for  $V_3$  Si there is a small deviation from the linear dependence at the highest pressure applied, but in view of the accompanying increase in transition width, its significance should be regarded as questionable. It may be noted that owing to the considerable anisotropy in the stress dependence<sup>8</sup> of  $T_c$  for  $V_3$  Si it would only require a 1-2% deviation from a uniform stress distribution within the sample to account for the deviation. However, for the purpose of demonstration we have constructed extreme fits to the data in which we include a guadratic term. A significant deviation from the straightline fit, in the pressure range of the measurements. only occurs for V<sub>3</sub>Si above 20 kbar. This is indicated in Fig. 1 by the broken line. The pressure derivatives and the corresponding elastic quantities calculated from (3) and (4) are listed in parentheses in Table II. Clearly, this approach has done little to improve the situation. Indeed, the introduction of the quadratic term has led, in both cases, to an increase in the linear term, thus compounding the discrepancy with the bulk modulus. Furthermore, the sign of the quadratic term for  $V_3$  Ge is opposite to that required by the elastic data.

As there can be no doubt that there is a substantial linear term in the pressure dependence of  $T_c$ , a discontinuity in bulk modulus is expected at the

TABLE II. Comparison of calculated and observed quantities from relationships (3) and (4).

	$\partial T_c / \partial P$ (10 <sup>-11</sup> deg cm <sup>2</sup> dyn <sup>-1</sup> )		$\partial^2 T_c / \partial P^2$ (10 <sup>-20</sup> deg cm <sup>4</sup> dyn <sup>-2</sup> )		$\beta_n - \beta_s$ (10 <sup>8</sup> dyn cm <sup>-2</sup> )		$\partial (\beta_n - \beta_s) / \partial T$ (10 <sup>8</sup> dyn cm <sup>-2</sup> deg <sup>-1</sup> )	
	Calculated	Observed	Calculated	Observed	Calculated	Observed	Calculated	Observed
V <sub>3</sub> Ge V <sub>3</sub> Si	$\leq \pm 2.56$ $\leq \pm 2.61$	8.1 (8.5) 3.7 (4.3)	0.69 -3.23	$\sim 0$ (-0.045) $\sim 0$ (-0.064)	-3.0 (-3.3) -1.8 (-2.4)	$ \leq 0.3 \\ \leq 0.91 $	1.4 (1.7) 0.3 (1.3)	-3.0 43



FIG. 1. Comparison of the directly measured variation of  $T_c$  with pressure (solid line) with that calculated from the elastic data (dotted line).

transition.<sup>9</sup> In the case of  $V_3$  Si this would only amount to the order of twice the resolution available in the elastic measurements and it therefore seems reasonable to assume that the effect was too small to be resolved. However, it is disturbing that there is no apparent evidence of a discontinuity in the elastic data for  $V_3$  Ge, since here the expected effect should be an order of magnitude greater than the resolution in the measurements.

In considering the discontinuity in the tempera-

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- <sup>1</sup>L. R. Testardi, J. E. Kunzler, H. J. Levinstein, and
- J. H. Wernick, Solid State Commun. 8, 907 (1970).
  - <sup>2</sup>L. R. Testardi, Phys. Rev. B <u>3</u>, 95 (1971).
- <sup>3</sup>L. R. Testardi, J. E. Kunzler, H. J. Levinstein, J. P. Maita, and J. H. Wernick, Phys. Rev. B <u>3</u>, 107 (1971). <sup>4</sup>Throughout we shall consider nontransforming V<sub>2</sub>Si.
- i.e., material which does not undergo the cubic-to-tetragonal transformation just above  $T_c$ .
  - <sup>5</sup>H. Neubauer, Z. Physik <u>226</u>, 211 (1969).
  - <sup>6</sup>T. F. Smith, Phys. Rev. Letters <u>25</u>, 1483 (1970).

ture derivatives of the bulk modulus we note that

$$\frac{\partial}{\partial T} (\beta_n - \beta_s) = \frac{\partial}{\partial T} (c_{11}^n - c_{11}^s) \\ - \frac{4}{3} \frac{\partial}{\partial T} \left[ \left( \frac{c_{11} - c_{12}}{2} \right)^n - \left( \frac{c_{11} - c_{12}}{2} \right)^s \right] ,$$

where the two terms on the right-hand side are almost equal. Thus, even a modest error in the determination of either, or both, of these terms could lead to a large error in their difference. In the particular case of  $V_3$  Ge a reduction of the first term by 30% or an increase of the second by 37%(or the appropriate combination of a  $\sim 15\%$  change in both) would reduce the predicted  $\partial^2 T_c / \partial P^2$  to zero. The corresponding changes for  $V_3Si$  would be somewhat greater, amounting to a 50% decrease of the first term or a 90% increase of the second. We may note that an analysis of thermal expansion measurements<sup>10</sup> on single-crystal V<sub>3</sub>Si provides support for the value of the latter (shear) term, as determined from the elastic measurements, which would suggest that the problem may lie almost entirely with the first term  $(c_{11})$ . Since the expansion measurements clearly show that even for a nominally nontransforming single crystal a small proportion of the crystal still undergoes the cubicto-tetragonal transition, the influence of the transformed material on the variation of  $c_{11}$  with temperature may well be quite significant.

In summary, it appears that a certain degree of reconciliation between the measured pressure dependence of  $T_c$  and that expected from a thermodynamic treatment of the elastic properties is possible, though unresolved discrepancies still exist for both compounds. A redetermination of the elastic behavior close to  $T_c$  is desirable, particularly for  $V_3$  Ge.

We wish to thank L. R. Testardi for stimulating correspondence and discussions.

<sup>7</sup>See, for example, D. Shoenberg, Superconductivity (Cambridge U. P., Cambridge, England, 1962), pp. 73– 75. It may be noted that in Testardi's treatment (Ref. 2) he considers this relationship to be the difference in Helmholtz free energy, thus effectively neglecting a term  $P(V_n - V_s)$ . This term is not important unless the P-vs-V relationship is very nonlinear.

<sup>8</sup>M. Weger, B. G. Silbernagle, and E. S. Greiner, Phys. Rev. Letters <u>1</u>3, 521 (1964).

<sup>9</sup>The discontinuity in the thermal expansion of  $V_3Si$  at  $T_c$  yields a value for  $\partial T_c/\partial P$  which is in reasonable agreement with that determined from the pressure measurements (Ref. 10).

<sup>10</sup>E. Fawcett, Phys. Rev. Letters <u>26</u>, 829 (1971).